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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in

the application:

LISTING OF CLAIMS:

Claims 1-14 (canceled).

Claim 15 (new): A branching filter comprising:

a transmitting filter; and

a receiving filter; wherein

piezoelectric thin film resonators including at least one piezoelectric thin film

sandwiched between at least one pair of opposed electrodes are arranged in a ladder

configuration on an opening or a recess of a substrate, the transmitting filter and the

receiving filter being connected to an antenna terminal in parallel; and

the piezoelectric thin film resonators defining the transmitting filter and the

piezoelectric thin film resonators defining the receiving filter have a different structure

from each other.

Claim 16 (new): The branching filter according to claim 15, wherein the

piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin

film resonators defining the receiving filter have different piezoelectric films.

Claim 17 (new): The branching filter according to claim 16, wherein the

piezoelectric film of the piezoelectric thin film resonators defining the transmitting filter

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includes AIN and the piezoelectric film of the piezoelectric thin film resonators defining

the receiving filter includes ZnO.

Claim 18 (new): The branching filter according to claim 15, wherein the material

of the electrodes is different between the piezoelectric thin film resonators defining the

transmitting filter and the piezoelectric thin film resonators defining the receiving filter.

Claim 19 (new): The branching filter according to claim 18, wherein the acoustic

impedance of the material of the electrodes is different between the piezoelectric thin

film resonators defining the transmitting filter and the piezoelectric thin film resonators

defining the receiving filter.

Claim 20 (new): The branching filter according to claim 18, wherein the

frequency of the pass band of the receiving filter is higher than the frequency of the

pass band of the transmitting filter, and the acoustic impedance of the material of the

electrodes defining the receiving filter is higher than the acoustic impedance of the

material of the electrodes defining the transmitting filter.

The branching filter according to claim 15, wherein the Claim 21 (new):

piezoelectric thin film resonators defining the transmitting filter use second harmonic

waves and the piezoelectric thin film resonators defining the receiving filter use

fundamental waves.

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Claim 22 (new): The branching filter according to claim 15, wherein the

piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin

film resonators defining the receiving filter further comprise a different insulating film on

the opening or the recess of the substrate.

Claim 23 (new): The branching filter according to claim 22, wherein the

insulating film of the piezoelectric thin film resonators defining the receiving filter

comprises SiO₂.

Claim 24 (new): The branching filter according to claim 22, wherein the

insulating film of the piezoelectric thin film resonators defining the receiving filter

comprises two layers including an SiO2 layer adjacent to the piezoelectric thin film and

an Al₂O₃ layer adjacent to the SiO₂ layer.

Claim 25 (new): The branching filter according to claim 22, wherein the insulating

film of the piezoelectric thin film resonators defining the receiving filter comprises two

layers including an SiO2 layer adjacent to the piezoelectric thin film and an AIN layer

adjacent to the SiO₂ layer.

Claim 26 (new): The branching filter according to claim 22, wherein the

insulating film of the piezoelectric thin film resonators defining the transmitting filter

comprises two layers including an AIN layer adjacent to the piezoelectric thin film and

an SiO₂ layer adjacent to the AlN layer.

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Claim 27 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the transmitting filter comprises two layers including an Al_2O_3 layer adjacent to the piezoelectric thin film and an SiO_2 layer adjacent to the Al_2O_3 layer.

Claim 28 (new): A communication device comprising the branching filter according to claim 15.